CLAIMS

What is claimed is:

1. A lithography method for selectively exposing parts of first and second targets, comprising:

performing a first patterning of a first target, wherein the first patterning includes:

directing light from a light source through a re-configurable reflective condenser in a first configuration to a first reflective reticle portion; and

reflecting the light from the first reflective reticle portion to a first target portion to be selectively exposed;

re-configuring the reflective condenser to a second configuration; and

performing a second patterning of a second target, wherein the second patterning includes:

directing light from a light source through the re-configurable reflective condenser in a second configuration to a second reflective reticle portion; and

reflecting the light from the second reflective reticle portion to a second target portion to be selectively exposed.

2. The method of claim 1, wherein the re-configuring includes configuring reflective facets of a multi-faceted mirror that is part of the reflective condenser.

3. The method of claim 2, wherein the configuring the facets includes using a controller that is coupled to the mirror to control the re-configuring the reflective facets.

4. The method of claim 3, wherein the controller is also operatively coupled to the reflective reticle portions.

5. The method of claim 2, wherein the configuring the facets includes selectively actuating piezoelectric pushers of the multi-faceted mirror, wherein each of the reflective facets has multiple of the piezoelectric pushers coupled thereto.

6. The method of claim 1, wherein the re-configuring from the first configuration of the reflective condenser to the second configuration of the reflective condenser results in a change of a degree of partial coherence of the light output from the reflective condenser.

7. The method of claim 1, wherein the re-configuring from the first configuration of the reflective condenser to the second configuration of the reflective condenser results in a change of a light distribution at the pupil.

8. The method of claim 1, wherein the light produced by the light source is extreme ultraviolet (EUV) radiation, having a wavelength in the range of about 30 to 700 Angstroms (3-70 nm).

9. The method of claim 1, wherein the first patterning and the second patterning includes passing the light through optics between the reticle portions and the targets.

10. The method of claim 1, wherein the reflective reticle portions are different portions of a single reflective reticle.

11. The method of claim 1, wherein the reflective reticle portions are portions of different reflective reticles.

12. The method of claim 1, wherein the target portions are wafer portions covered with resist.

13. The method of claim 12, wherein the wafer portions are portions of a single wafer.

14. The method of claim 12, wherein the wafer portions are portions of different wafers.

15. A method of lithography comprising:

re-configuring, between lithography operations, reflective facets of a multi-faceted mirror that is part of a reflective condenser, wherein the re-configuring results in altering of light characteristics of light exiting the reflective condenser to strike a reflective reticle.

16. The method of claim 15, wherein the re-configuring results in changing a degree of partial coherence of the light.

17. The method of claim 15, wherein the re-configuring results in changing a distribution of light at the pupil of the imaging system.

18. The method of claim 15, further comprising performing one of the lithography operations prior to the re-configuring, and performing another of the lithography operations after the configuring.

19. A lithography system comprising:

a light source;

a reflective reticle; and

a re-configurable reflective condenser that directs light from the light source to the reflective reticle;

wherein the reflective condenser includes a re-configurable multi-faceted mirror.